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HBD140

PNP POWER TRANSISTORS

Description

PNP power transistor in a TO-126 plastic package. NPN complements: HBD139

Features

- High Current (max. 1.5A)
- Low Voltage (max. 80V)



General purpose power applications, e.g. driver stages in hi-fi amplifiers and television circuits.

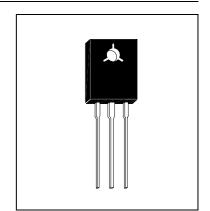
Limiting Values

Symbol	Parametor	Conditions	Min.	Max.	Unit
VCBO	Collector-Base Voltage	Open Emitter	-	-100	V
VCEO	Collector-Emitter Voltage	Open Base	-	-80	V
VEBO	Emitter-Base Voltage	Open Collector	-	-5	V
IC	Collector Current (DC)		-	-1.5	Α
ICM	Peak Collector Current		-	-2	Α
IBM	Peak Base Current		-	-1	Α
PD	Total Dissipation at	Ta=25°C	-	1.2	W
PD		Tc=25°C	-	15	W
Tstg	Storage Temperature	-	-65	150	°C
Tj	Junction Temperature	-	-	150	°C
Tamb	Operating Ambient Temperature	-	-65	150	°C

Electrical Characteristics (Tj=25°C, unless otherwise specified)

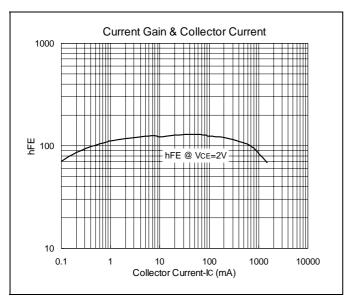
Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
ICBO	Collector Cut-off Current	IE=0, VCB=-30V	-	-	-100	nA
IEBO	Emitter Cut-off Current IC=0, VEB=-5V		1	-	-100	nA
*VCE(sat)	Collector-Emitter Saturation Voltage IC=-500mA, IB=-50mA		-	-	-0.5	V
*VBE	Base-Emitter Voltage IC=-500mA, VCE=-2V		•	-	-1	V
hFE	DC Current Gain	VCE=-2V, IC=-5mA	40	-	-	-
		VCE=-2V, IC=-150mA	63	-	250	-
		VCE=-2V, IC=-500mA,	25	-	-	-
fT	Transition Frequency IC=-50mA, VCE=-5V, f=10		ı	230	-	MHz
*hFE1/hFE2	DC current gain ratio of the complementary pairs	IC =150mA, VCE =2V	ı	1	1.6	-

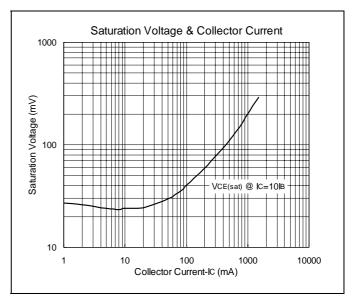
*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%

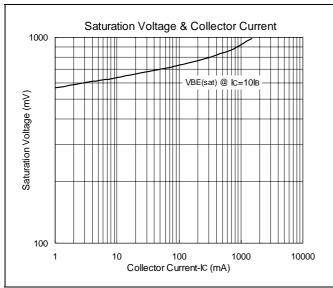


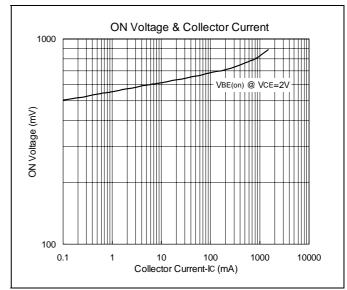
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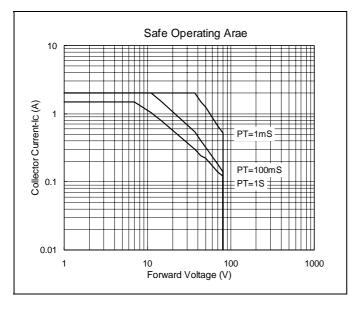
Characteristics Curve







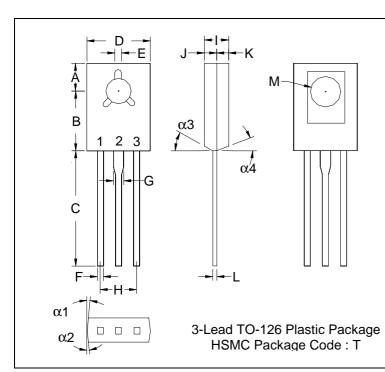




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TO-126 Dimension



Marking: H B D 1 4 0 Control Code Laser Marking

Style: Pin 1.Emitter 2.Collector 3.Base

*:Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.	DIIVI	Min.	Max.	Min.	Max.
α1	-	*3°	-	*3°	F	0.0280	0.0319	0.71	0.81
α2	-	*3°	-	*3°	G	0.0480	0.0520	1.22	1.32
α3	-	*3°	-	*3°	Н	0.1709	0.1890	4.34	4.80
α4	-	*3°	-	*3°	I	0.0950	0.1050	2.41	2.66
Α	0.1500	0.1539	3.81	3.91	J	0.0450	0.0550	1.14	1.39
В	0.2752	0.2791	6.99	7.09	K	0.0450	0.0550	1.14	1.39
С	0.5315	0.6102	13.50	15.50	L	-	*0.0217	ı	*0.55
D	0.2854	0.3039	7.52	7.72	M	0.1378	0.1520	3.50	3.86
Е	0.0374	0.0413	0.95	1.05					

Notes: 1.Dimension and tolerance based on our Spec. dated Mar. 6,1995.

- 2. Controlling dimension: millimeters.
- 3.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
- 4.If there is any question with packing specification or packing method, please contact your local HSMC sales office.

Material:

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class:UL94V-0

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Head Office And Factory :

- Head Office (Hi-Sincerity Microelectronics Corp.): 10F.,No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C. Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- Factory 1: No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C

Tel: 886-3-5983621~5 Fax: 886-3-5982931